

## Inorganic nanostructured solar cells

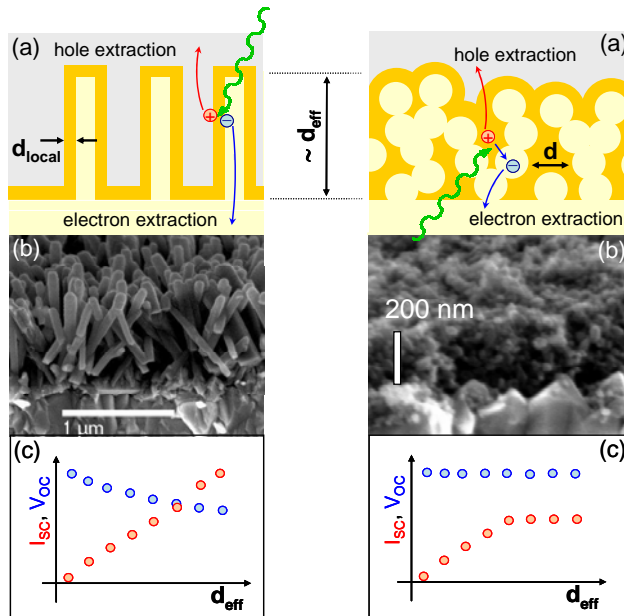
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**Abstract** – The realization of low-cost solar cells depends on the realization of low processing temperatures. The diffusion length of photo-generated charge carriers in the absorber material is one of the most important parameters for solar cells. Low temperature processes result usually in very low diffusion lengths of inorganic absorbers. Nanostructures can help to overcome problems with the diffusion length. Here we compare the concepts of inorganic solid state solar cells with extremely thin absorber and ultra-thin nanocomposite absorber on the examples of ZnO-nanorod/ $\text{In}_2\text{S}_3$ /CuSCN and nanoporous- $\text{TiO}_2$ / $\text{In}_2\text{S}_3$ /CuSCN systems.

Figures 1(a) and 2(a) show the schematic cross sections of solar cells with extremely thin absorber ( $d_{\text{eta}}$ ) and with ultra-thin nanocomposite absorber, respectively. The extremely thin absorber is folded following the morphology of a template, for example the surface of a ZnO nanorod array (fig.1(b)). The nanocomposite absorber consists of a nanoporous matrix, for example of interconnected  $\text{TiO}_2$  nanoparticles (fig.2 (b)), with an absorbing material filling the pores completely. The local absorber layer thickness ( $d_{\text{local}}$ ) has to be larger than the tunneling length between the electron and hole extracting contacts but less than the transport or diffusion length of photo-generated charge carriers. The pore size of the nanoporous matrix has to be less than half of the transport length in the absorbing material. The nanocomposite absorber can be considered as an effective absorber layer with its own diffusion length. The diffusion length of the nanocomposite absorber can be much larger than the transport length of the absorber material due to local charge separation and separate percolating transport paths for electrons and holes. The short circuit current ( $I_{\text{SC}}$ ) of the  $\eta$ a solar cell scales with the surface area of the template, i.e.  $d_{\text{eff}}$  (fig.1.(c)).  $I_{\text{SC}}$  of the nanocomposite absorber solar cell is limited by the diffusion length, i.e.  $I_{\text{SC}}$  saturates for large values of  $d_{\text{eff}}$  (fig.2(c)). Recombination increases with increasing area of the limiting contact. Therefore, the open circuit voltage ( $V_{\text{OC}}$ ) may not increase or even decrease with increasing  $d_{\text{eff}}$  for  $\eta$ a solar cells or solar cells with nanocomposite absorbers (fig.1 (c), 2 (c)).



**Figure 1:** a) Schematic cross section of a solar cell with extremely thin absorber. b) Electron microscopy cross section of a ZnO nanorod array with a 30 nm thick  $\text{In}_2\text{S}_3$  coating. c) Principle dependencies of the short circuit current and of the open circuit voltage on the effective layer thickness.

**Figure 2:** a) Schematic cross section of a solar cell with ultra-thin nanocomposite absorber. b) Electron microscopy cross section of a nanoporous  $\text{TiO}_2$  layer. c) Principle dependencies of the short circuit current and of the open circuit voltage on the effective layer thickness.

Small area solar cells with extremely thin  $\text{In}_2\text{S}_3$  absorber based on ZnO nanorod-arrays [1,2] and with ultra-thin  $\text{TiO}_2$ / $\text{In}_2\text{S}_3$  nanocomposite absorbers [3] as model systems were realized to demonstrate the basic dependencies of  $I_{\text{SC}}$  and  $V_{\text{OC}}$  on  $d_{\text{local}}$  and on  $d_{\text{eff}}$ . CuSCN was used as the hole extracting contact. The transport

length of the wet chemically prepared  $\text{In}_2\text{S}_3$  absorber was of the order of 20-30 nm whereas the diffusion length of the nanocomposite absorber increased by about one order of magnitude. The hole extracting contact is the critical one in the investigated systems. Possible measures to increase the energy conversion efficiency as well as the opportunity to implement absorbing semiconductor nanoparticles will be discussed.

### References

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